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THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Matthias Passlack et al.

) Patent No.: 6,756,320 B2

Application No.: 10/051,494

) Issue Date: June 29, 2004

Filed: January 18, 2002

) Docket No.: SC11692ZP

Title: ARTICLE COMPRISING AN OXIDE LAYER ON A GAAS-BASED  
SEMICONDUCTOR STRUCTURE

Certificate of Mailing

Date of deposit: 4-3-06

I hereby certify that this paper is being deposited with the United States Postal Service on the date indicated above, as first-class mail, with sufficient postage attached thereto, in an envelope addressed to the Commissioner for Patents, Alexandria, VA 22313.

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Certificate of Corrections Branch  
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Alexandria, VA 22313

**Certificate**  
**APR 11 2006**  
**of Correction**

SUBMISSION OF CERTIFICATE OF CORRECTION

Dear Commissioner:

Enclosed, in duplicate, is a Certificate of Correction for errors in the subject patent.  
Please enter these corrections.

Since the errors appear to be on the part of the United States Patent Office, there should be no charge.

Respectfully submitted,

3/31/06  
Date

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PTO/SB/ 44 (04-05)

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CERTIFICATE OF CORRECTION**

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DATE: June 29, 2004  
INVENTOR(S): Matthias Passlack et al.

It is certified that error appears in the above-identified patent and that said Letters Patent are hereby corrected as shown below:

In Column 6, Line 33, change "Ga<sup>2</sup>O<sup>3</sup>" to - -Ga<sub>2</sub>O<sub>3</sub> - -

In Column 6, Line 34, after "material" insert - -of Ga-Gd oxide- -

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